

General Description

The G1005 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a load switch or in PWM applications.

General Features

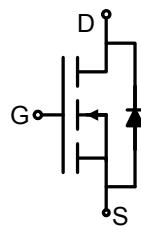
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V_{DSS}	$R_{DS(ON)}$ @ 10V (Typ)	I_D
100V	123mΩ	5 A

- High Power and current handing capability
- RoHS Compliant
- Surface Mount Package

Application

- PWM applications
- Load switch
- Power management

**Schematic diagram****TO-92****Ordering Information**

Part Number	Marking	Case	Packaging
G1005	G1005	TO-92	1000pcs/Carton

Table 1. Absolute Maximum Ratings ($T_A=25^\circ C$)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage ($V_{GS}=0V$)	100	V
V_{GS}	Gate-Source Voltage ($V_{DS}=0V$)	± 20	V
I_D	Drain Current-Continuous($T_c=25^\circ C$)	5	A
	Drain Current-Continuous($T_c=100^\circ C$)	3.1	A
I_{DM} (pulse)	Drain Current-Continuous@ Current-Pulsed (Note 1)	20	A
P_D	Maximum Power Dissipation	9.3	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	°C

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

Table 2. Thermal Characteristic

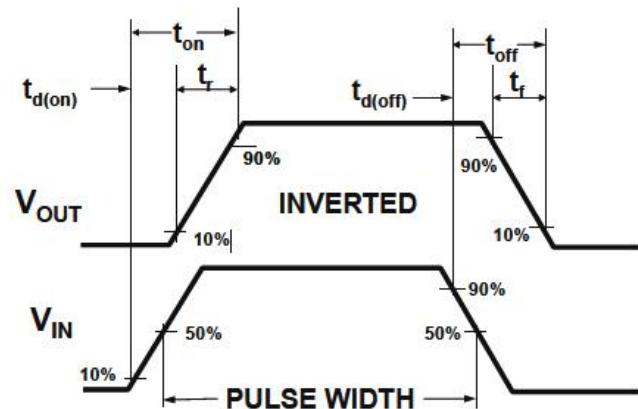
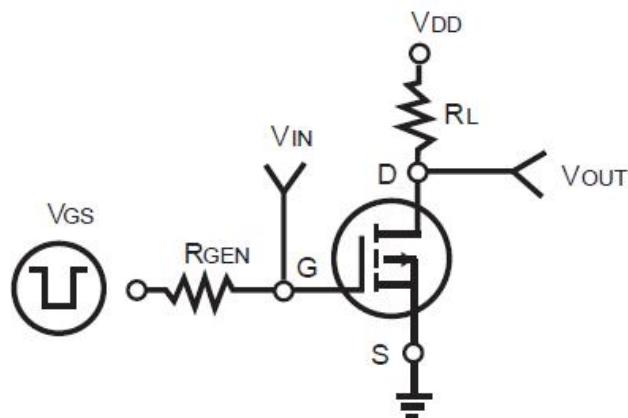
Symbol	Parameter	Typ	Value	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	-	13.5	°C/W

Table 3. Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}$, $I_{\text{D}}=250\mu\text{A}$	100			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{\text{DS}}=100\text{V}$, $V_{\text{GS}}=0\text{V}$			0.9	μA
I_{GSS}	Gate-Body Leakage Current	$V_{\text{GS}}=\pm 20\text{V}$, $V_{\text{DS}}=0\text{V}$			± 100	nA
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}$, $I_{\text{D}}=250\mu\text{A}$	1.3	1.9	2.5	V
$R_{\text{DS(ON)}}$	Drain-Source On-State Resistance	$V_{\text{GS}}=10\text{V}$, $I_{\text{D}}=3\text{A}$		123	180	$\text{m}\Omega$
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{\text{DS}}=25\text{V}$, $V_{\text{GS}}=0\text{V}$, $f=1.0\text{MHz}$		690		pF
C_{oss}	Output Capacitance			120		pF
C_{rss}	Reverse Transfer Capacitance			90		pF
Switching Times						
$t_{\text{d(on)}}$	Turn-on Delay Time	$V_{\text{DD}}=15\text{V}$, $I_{\text{D}}=1\text{A}$, $R_{\text{L}}=15\Omega$ $V_{\text{GS}}=10\text{V}$, $R_{\text{G}}=2.5\Omega$		11		nS
t_r	Turn-on Rise Time			7.4		nS
$t_{\text{d(off)}}$	Turn-Off Delay Time			35		nS
t_f	Turn-Off Fall Time			9.1		nS
Q_g	Total Gate Charge	$V_{\text{DS}}=15\text{V}$, $I_{\text{D}}=5\text{A}$ $V_{\text{GS}}=10\text{V}$		15.5		nC
Q_{gs}	Gate-Source Charge			3.2		nC
Q_{gd}	Gate-Drain Charge			4.7		nC
Source-Drain Diode Characteristics						
I_{SD}	Source-Drain Current(Body Diode)				5	A
V_{SD}	Forward on Voltage ^(Note 1)	$V_{\text{GS}}=0\text{V}$, $I_{\text{S}}=3\text{A}$			1	V

Notes 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

Switch Time Test Circuit and Switching Waveforms:



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (Curves)

Figure1. Output Characteristics

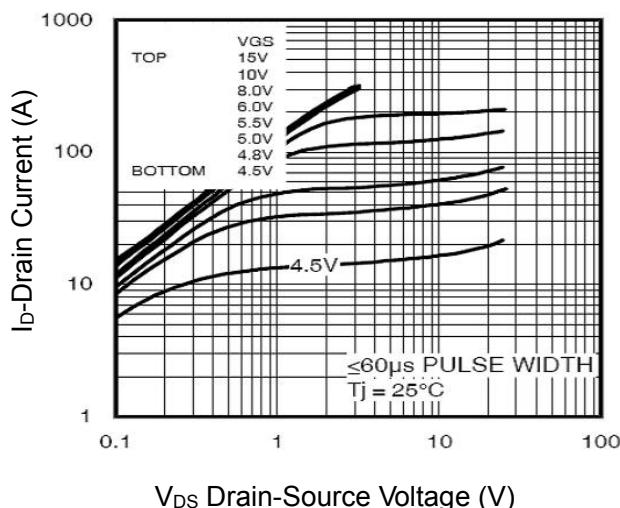


Figure2. Transfer Characteristics

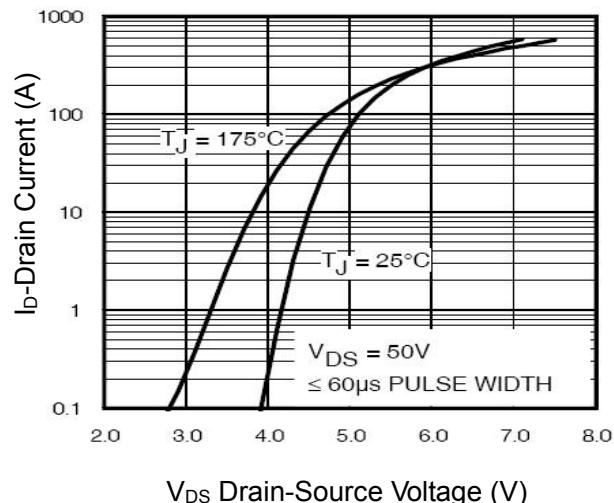


Figure3. BVDSS vs Junction Temperature

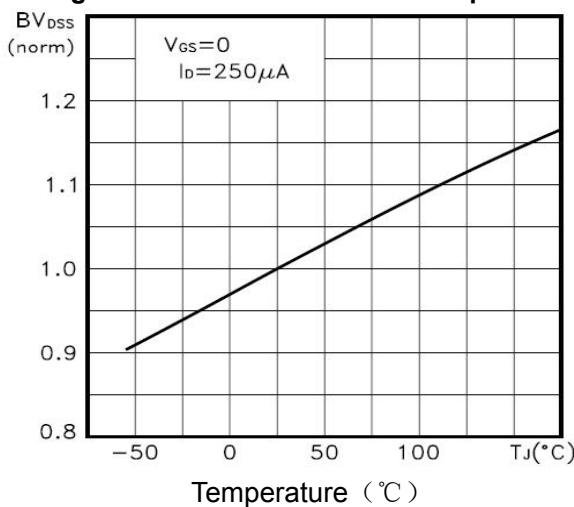


Figure4. ID vs Junction Temperature

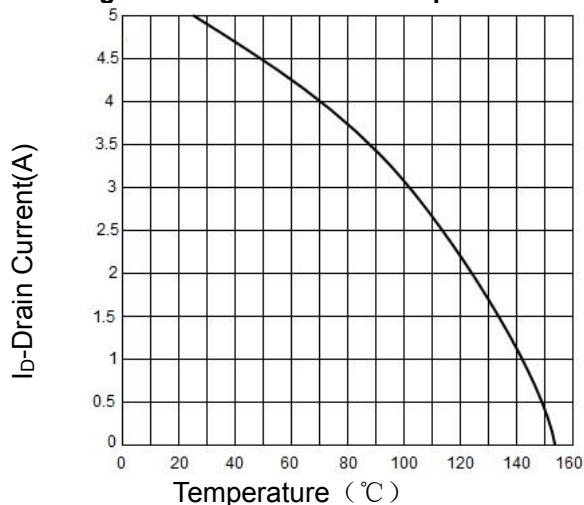


Figure5. VGS(th) vs Junction Temperature

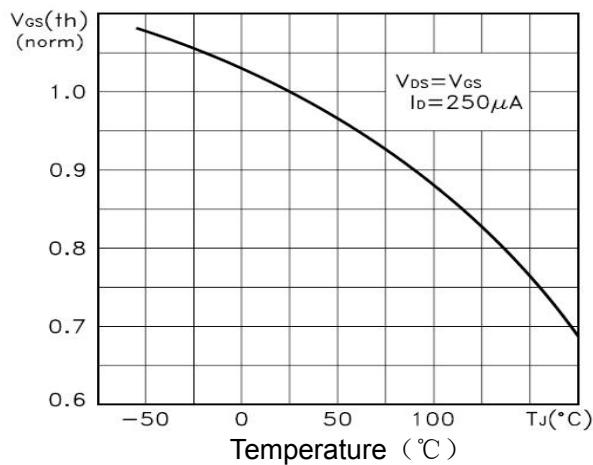


Figure6. Rdson Vs Junction Temperature

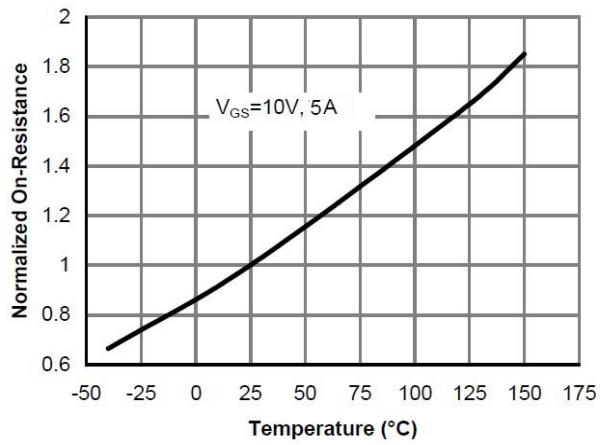


Figure7. Gate Charge

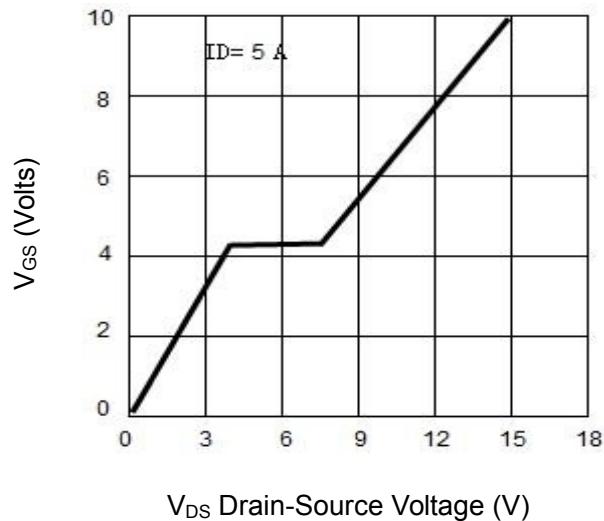


Figure8. Capacitance vs Vds

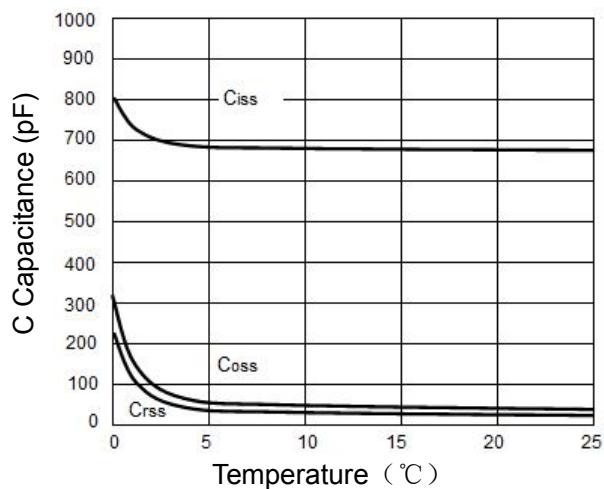


Figure9. Source- Drain Diode Forward

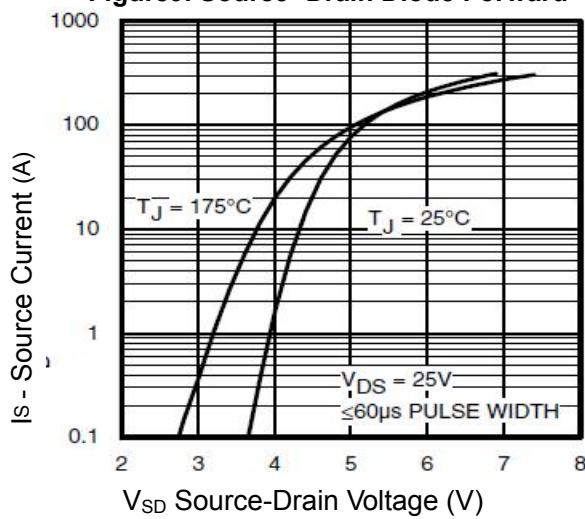


Figure10. Safe Operation Area

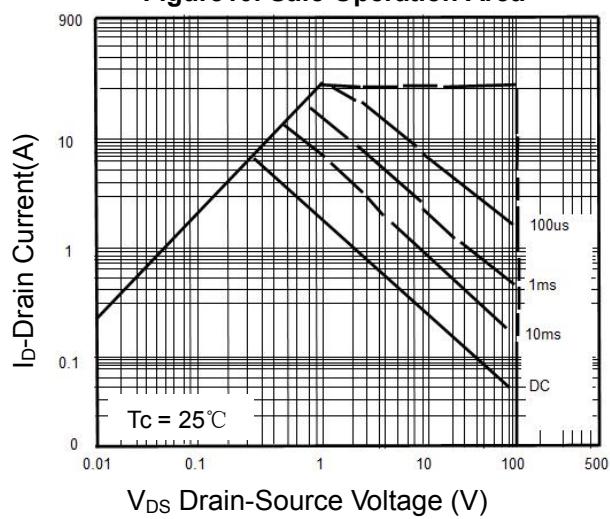
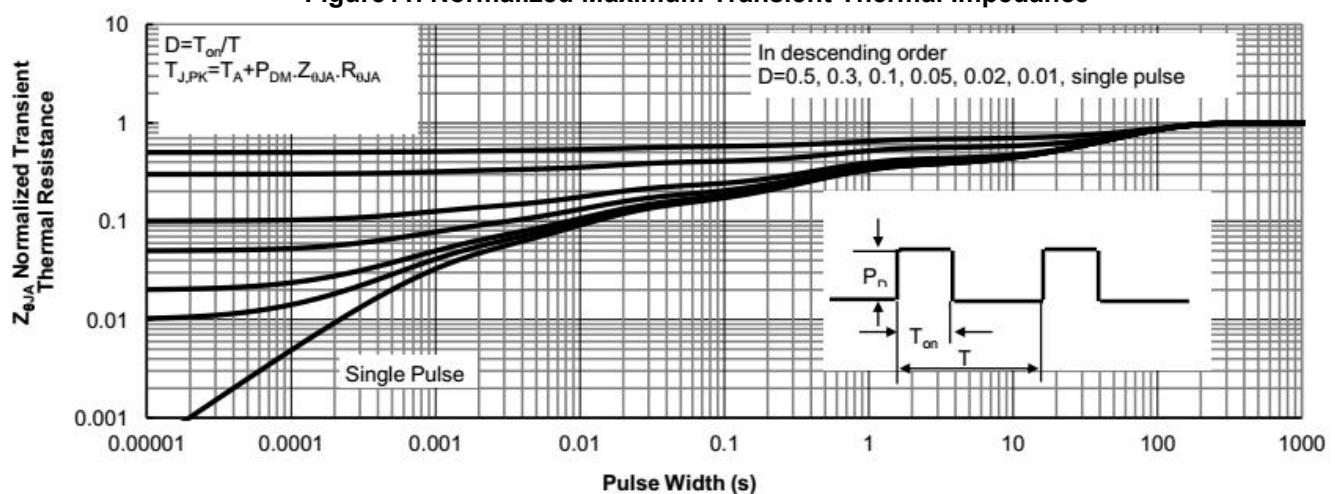
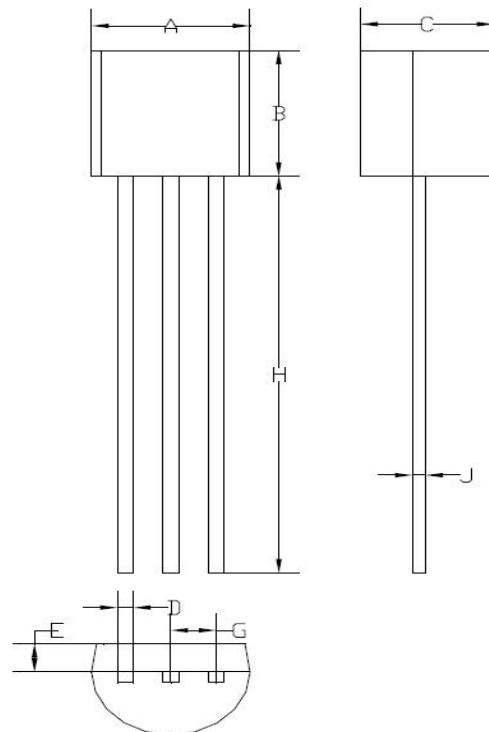


Figure11. Normalized Maximum Transient Thermal Impedance

TO-92 Package information

TO-92			
Dim	MIN	NOM	MAX
A	4.59	4.60	-
B	4.58	4.60	4.62
C	3.50	3.55	3.60
D	2.50	2.55	2.60
E	-	1.25	1.30
G	1.24	1.27	1.30
H	14.28	14.30	14.32
J	0.38		
All Dimensions in mm			